

Vishay Siliconix

# 3- $\Omega$ , High Bandwidth, Dual SPDT Analog Switch

### DESCRIPTION

The DG2517, DG2518 are low-voltage dual single-pole/ double-throw monolithic CMOS analog switches. Designed to operate from 1.8 V to 5.5 V power supply, the DG2517, DG2518 achieves a bandwidth of 242 MHz while providing low on-resistance (3  $\Omega$ ), excellent on-resistance matching (0.2  $\Omega$ ) and flatness (1  $\Omega$ ) over the entire signal range.

The DG2517, DG2518 offers the advantage of high linearity that reduces signal distortion, making ideal for audio, video, and USB signal routing applications. Additionally, the DG2517, DG2518 are 1.6 V logic compatible within the full operation voltage range.

Built on Vishay Siliconix's proprietary sub-micron highdensity process, the DG2517, DG2518 brings low power consumption at the same time as reduces PCB spacing with the MSOP10 and DFN10 packages.

As a committed partner to the community and the environment, Vishay Siliconix manufactures this product with the lead (Pb)-free device terminations. The DFN package has a nickel-palladium-gold device termination and is represented by the lead (Pb)-free "-E4" suffix. The MSOP package uses 100 % matte Tin device termination and is represented by the lead (Pb)- free "-E3" suffix. Both the matte Tin and nickel-palladium-gold device terminations meet all JEDEC standards for reflow and MSL ratings.

#### FEATURES

- 1.8 V to 5.5 V single supply operation
- Low  $R_{ON}$ : 3  $\Omega$  at 4.2 V
- 242 MHz, 3 dB bandwidth
- Low off-isolation, 51 dB at 10 MHz
- + 1.6 V logic compatible

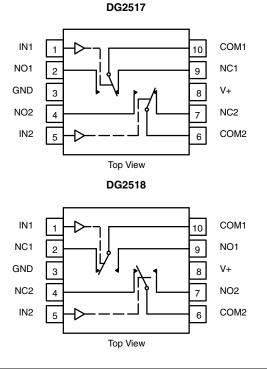
#### BENEFITS

- High linearity
- Low power consumption
- High bandwidth
- Full rail signal swing range

#### **APPLICATIONS**

- USB/UART signal switching
- Audio/video switching
- Cellular phone
- Media players
- Modems
- · Hard drives
- PCMCIA

### FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



TRUTH TABLE						
Logic	NC1 and NC2	NO1 and NO2				
0	ON	OFF				
1	OFF	ON				

ORDERING INFORMATION						
Temp. Range Package Part Number						
	MSOP-10	DG2517DQ-T1-E3				
- 40 °C to 85 °C	WISOF-10	DG2518DQ-T1-E3				
- 40 °C to 85 °C	DEN-10	DG2517DN-T1-E4				
	DFN-10	DG2518DN-T1-E4				



COMPLIANT

## **Vishay Siliconix**



### **ABSOLUTE MAXIMUM RATINGS**

	IIIIII			
Parameter	Limit	Unit		
Reference to GND				
V+	- 0.3 to + 6	V		
IN, COM, NC, NO <sup>a</sup>	- 0.3 to (V+ + 0.3)			
Continuous Current (Any terminal)	± 50	mA		
Peak Current (Pulsed at 1 ms, 10 % du	± 200	IIA		
Storage Temperature (D Suffix)	- 65 to 150	°C		
Power Dissipation (Packages) <sup>b</sup>	MSOP-10 <sup>c</sup>	320	mW	
	DFN-10 <sup>d</sup>	1191	11100	

Notes: a. Signals on NC, NO, or COM or IN exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings. b. All leads welded or soldered to PC board. c. Derate 4.0 mW/°C above 70 °C. d. Derate 14.9 mW/°C above 70 °C.

		Test Condition Otherwise Unless Sp		Limits - 40 °C to 85 °C					
Parameter	Symbol	$V + = 3 V, \pm 10 \%, V_{IN} = 0$	Temp. <sup>a</sup>	Min. <sup>b</sup>	Typ. <sup>c</sup>	Max. <sup>b</sup>	Unit		
Analog Switch									
Analog Signal Range <sup>d</sup>	V <sub>NO</sub> , V <sub>NC</sub> , V <sub>COM</sub>		Full	0		V+	V		
On-Resistance	R <sub>ON</sub>	V+ = 2.7 V, V <sub>COM</sub> = I <sub>NO/NC</sub> = 10 m/	Room Full		3.2	4.5 5.0			
R <sub>ON</sub> Flatness	R <sub>ON</sub> Flatness	V+ = 2.7 V, V <sub>COM</sub> = 1 I <sub>NO/NC</sub> = 10 m/	Room Full		1.0	1.4 16	Ω		
R <sub>ON</sub> Match Between Channels	$\Delta R_{ON}$	V+ = 2.7 V, V <sub>COM</sub> = I <sub>NO/NC</sub> = 10 m/	$V_{+} = 2.7 V. V_{COM} = 1.5 V$			0.1	0.3 0.4		
Switch Off Leakage Current <sup>f</sup>	I <sub>NO(off),</sub> I <sub>NC(off)</sub>	V+ = 3.6 V, V <sub>NO</sub> , V <sub>NC</sub> = 0.3 V/3 V V <sub>COM</sub> = 3 V/0.3 V		Room Full	- 1 - 10		1 10		
Switch On Leakage Suitent	I <sub>COM(off)</sub>	V <sub>COM</sub> = 3 V/0.3	V	Room Full	- 1 - 10		1 10	nA	
Channel-On Leakage Current <sup>f</sup>	I <sub>COM(on)</sub>	$V_{+} = 3.6 V, V_{NO}, V_{NC} = V_{CC}$	Room Full	- 1 - 10		1 10	1		
Digital Control									
Input High Voltage <sup>d</sup>	V <sub>INH</sub>				1.4			v	
Input Low Voltage	V <sub>INL</sub>			Full			0.5	v	
Input Capacitance	C <sub>in</sub>			Full		4		pF	
Input Current	I <sub>INL</sub> or I <sub>INH</sub>		Full	1		1	μA		
Dynamic Characteristics									
Turn-On Time	t <sub>ON</sub>	V+ = 2.7 V, $V_{NO}$ or $V_{NO}$	<sub>C</sub> = 1.5 V	Room Full		15	30 50	ns	
Turn-Off Time	t <sub>OFF</sub>	R <sub>L</sub> = 300 Ω, C <sub>L</sub> = 3	85 pF	Room Full		10	25 35		
Break-Before-Make Time	t <sub>d</sub>	$V_{NO} \text{ or } V_{NC} = 1.5 \text{ V}, \text{ R}_{L} = 300$		Full	1			1	
Charge Injection <sup>d</sup>	Q <sub>INJ</sub>	C <sub>L</sub> = 1 nF, V <sub>GEN</sub> = 1.5 V,		Room		1		рС	
- 3 dB Bandwidth	BW	0 dBm, $C_L = 5 \text{ pF}$ , $R_L$	= 50 Ω	Room		242		MH:	
Off-Isolation <sup>d</sup>	on <sup>d</sup> OIRR	R $R_L = 50 \Omega, C_L = 5 pF$	f = 1 MHz	Room		- 71		1	
On-Isolation			f = 10 MHz	Room		- 51		dB	
Crosstalk <sup>d</sup>	X <sub>TALK</sub>	D 5000 5-5	f = 1 MHz	Room		- 73		UD	
Olosian	MALK	$R_L = 50 \Omega$ , $C_L = 5 pF$	f = 10 MHz	Room		- 55			
N <sub>O</sub> , N <sub>C</sub> Off Capacitance <sup>d</sup>	C <sub>NO(off)</sub>	V <sub>IN</sub> = 0 or V+, f = 1 MHz		Room		8			
	C <sub>NC(off)</sub>			Room		8		pF	
Channel-On Capacitance <sup>d</sup>	C <sub>NO(on)</sub>	VIN - 0 01 VT, I - 1	1011 12	Room		35		P	
•	C <sub>NC(on)</sub>	<u> </u>		Room		35			
Power Supply									
Power Supply Current	l+	$V_{IN} = 0 \text{ or } V_{+}$	Full		0.01	1.0	μA		

Notes:

Notes: a. Room = 25 °C, Full = as determined by the operating suffix. b. Typical values are for design aid only, not guaranteed nor subject to production testing. c. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet. d. Guarantee by design, nor subjected to production test. e. V<sub>IN</sub> = input voltage to perform proper function. f. Guaranteed by 5 V leakage testing, not production tested.



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SPECIFICATIONS (V+	= 5 V							-
		Test Condition Otherwise Unless Sp		<b>Limits</b> - 40 °C to 85 °C				
Parameter	Symbol			Temp. <sup>a</sup>	Min. <sup>b</sup>	Typ. <sup>c</sup>	Max. <sup>b</sup>	Unit
Analog Switch		•						
Analog Signal Range <sup>d</sup>	V <sub>NO</sub> , V <sub>NC</sub> , V <sub>COM</sub>		Full	0		V+	V	
On-Resistance	R <sub>ON</sub>	$V_{+} = 4.2 V, V_{COM} = 3.5 V, I_{N}$	Room Full		3	4.0 4.3		
R <sub>ON</sub> Flatness	R <sub>ON</sub> Flatness	•••···	V+ = 4.2 V, V <sub>COM</sub> = 1, 2, 3.5 V $I_{NO/NC} = 10 \text{ mA}$			1.1	1.4 1.6	Ω
R <sub>ON</sub> Match Between Channels	$\Delta R_{ON}$	$V_{+} = 4.2 \text{ V}, V_{COM} = 3.5 \text{ V}, I_{N}$	Room Full		0.1	0.3 0.4		
Switch Off Leakage Current	I <sub>NO(off),</sub> I <sub>NC(off)</sub>	V+ = 5.5 V		Room Full	- 1 - 10		1 10	
Switch On Leakage Suitchit	I <sub>COM(off)</sub>	$V_{\rm NO}, V_{\rm NC} = 1 \text{ V}/4.5 \text{ V}, V_{\rm COI}$	<sub>M</sub> = 4.5 V/1 V	Room Full	- 1 - 10		1 10	nA
Channel-On Leakage Current	I <sub>COM(on)</sub>	$V$ + = 5.5 V, $V_{COM}$ = $V_{NO}$ , $V_{NC}$ = 1 V/4.5 V		Room Full	- 1 - 10		1 10	
Digital Control	•	•						
Input High Voltage <sup>d</sup>	V <sub>INH</sub>			Full	2.0			v
Input Low Voltage	V <sub>INL</sub>			Full			0.8	v
Input Capacitance	C <sub>in</sub>			Full		4		pF
Input Current	$I_{\rm INL}$ or $I_{\rm INH}$	V <sub>IN</sub> = 0 V or V-	÷	Full	1		1	μΑ
Dynamic Characteristics		•					•	
Turn-On Time	t <sub>ON</sub>	V+ = 4.2 V, V <sub>NO</sub> or V <sub>N</sub>	-	Room Full		12	25 45	
Turn-Off Time	t <sub>OFF</sub>	R <sub>L</sub> = 300 Ω, C <sub>L</sub> = 3		Room Full		8	20 30	ns
Break-Before-Make Time	t <sub>d</sub>	$V_{NO}$ or $V_{NC}$ = 3 V, $R_L$ = 300	Ω, C <sub>L</sub> = 35 pF	Full	1			
Charge Injection <sup>d</sup>	Q <sub>INJ</sub>	C <sub>L</sub> = 1 nF, V <sub>GEN</sub> = 2.5 V, I	$R_{GEN} = 0 \Omega$	Room		2		рС
- 3 dB Bandwidth	BW	0 dBm, $C_L = 5 \text{ pF}, R_L$	= 50 Ω	Room		242		MHz
Off-Isolation <sup>d</sup>	OIRR	$R_L = 50 $ Ω, $C_L = 5 $ pF	f = 1 MHz f = 10 MHz	Room Room		- 71 - 51		
Crosstalk <sup>d</sup>	X <sub>TALK</sub>	R <sub>L</sub> = 50 Ω, C <sub>L</sub> = 5 pF	f = 1 MHz f = 10 MHz	Room		- 73 - 55		dB
Course Off Conseitoneed	C <sub>NO(off)</sub>			Room		8		
Source-Off Capacitance <sup>d</sup>	C <sub>NC(off)</sub>	V <sub>IN</sub> = 0 or V+, f = 1 MHz		Room		8		~F
	C <sub>NO(on)</sub>			Room		35		pF
Channel-On Capacitance <sup>d</sup>	C <sub>NC(on)</sub>			Room		35		
Power Supply								
Power Supply Range	V+				1.8		5.5	V
Power Supply Current	l+	V <sub>IN</sub> = 0 or V+		Full		0.01	1.0	μA

Notes:

a. Room = 25  $^{\circ}$ C, Full = as determined by the operating suffix.

b. Typical values are for design aid only, not guaranteed nor subject to production testing.

c. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.

d. Guarantee by design, nor subjected to production test.

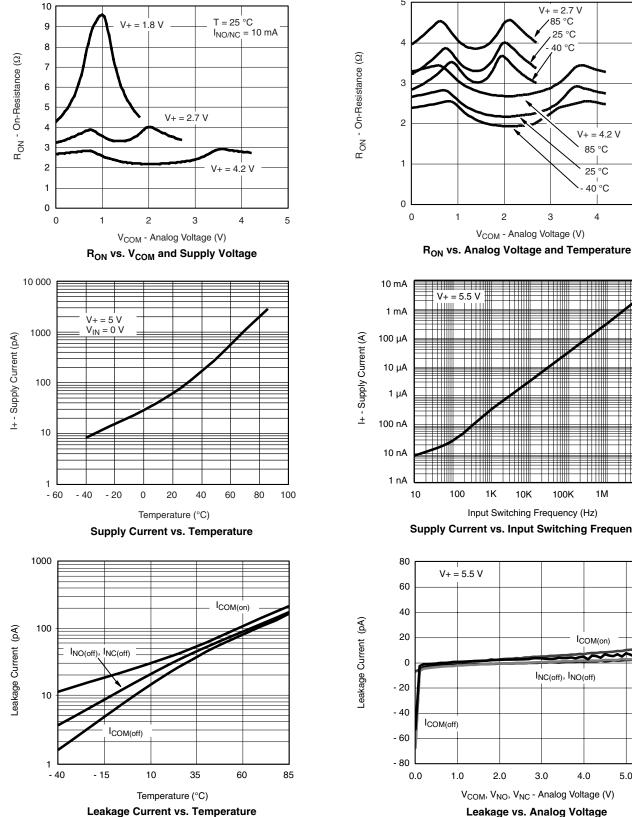
e. V<sub>IN</sub> = input voltage to perform proper function.

f. Guaranteed by 5 V leakage testing, not production tested.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



V+ = 2.7 V ′85 °C 25 °C 40 °C

3

V+ = 4.2 V

85 °C

25 °C

40 °C

4

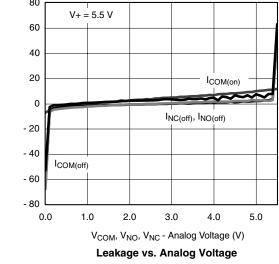
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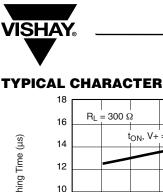
5

ISHA

-----10K 100K 1M 10M Input Switching Frequency (Hz)

Supply Current vs. Input Switching Frequency



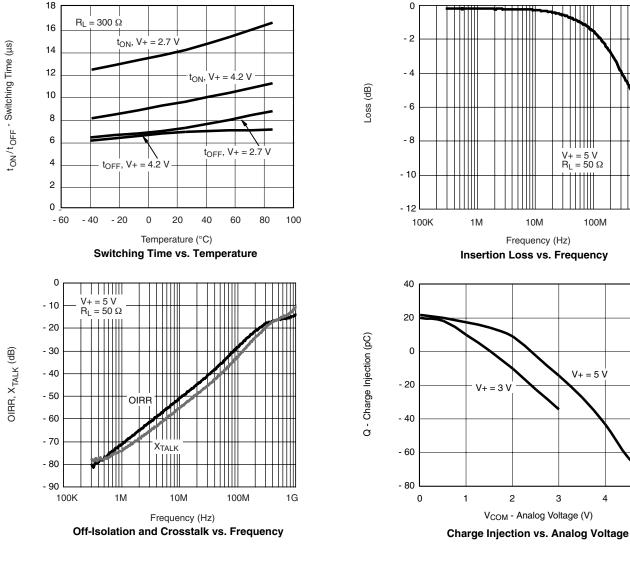


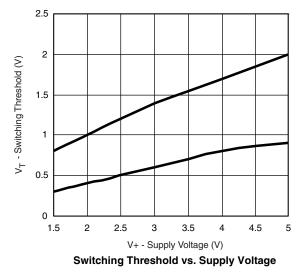
Vishay Siliconix

1G

5

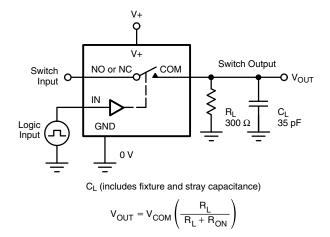
### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

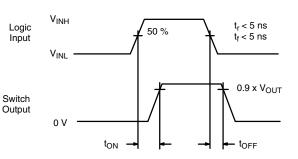




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### **TEST CIRCUITS**





Logic "1" = Switch On Logic input waveforms inverted for switches that have the opposite logic sense.



Logic

Input

 $V_{NC} = V_{NO}$ 

Switch 0 V

Output

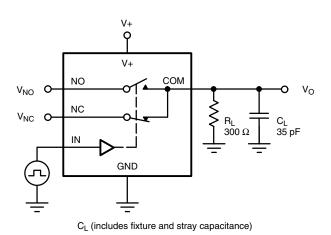
V<sub>INH</sub>

 $V_{\text{INL}}$ 

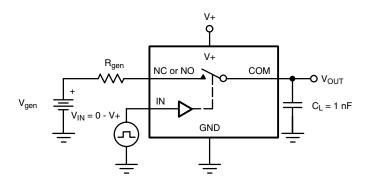
Vo

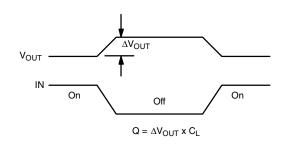
90 %

t<sub>D</sub>









IN depends on switch configuration: input polarity determined by sense of switch.

Figure 3. Charge Injection





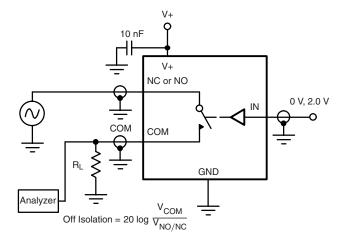
t<sub>r</sub> < 5 ns t<sub>f</sub> < 5 ns

t<sub>D</sub>



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### **TEST CIRCUITS**



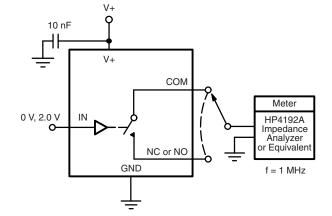




Figure 5. Channel Off/On Capacitance

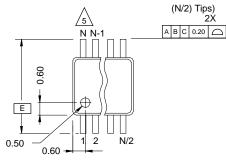
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see http://www.vishay.com/ppg?74333.



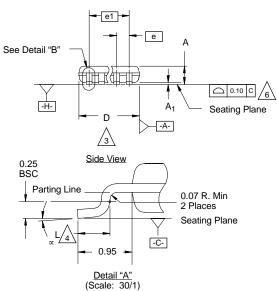
## Package Information Vishay Siliconix

#### MSOP: 10-LEADS

JEDEC Part Number: MO-187, (Variation AA and BA)







#### NOTES:

/4.\

/5.\

1. Die thickness allowable is  $0.203 \pm 0.0127$ .

2. Dimensioning and tolerances per ANSI.Y14.5M-1994.

/3. Dimensions "D" and "E<sub>1</sub>" do not include mold flash or protrusions, and are measured at Datum plane \_-H- , mold flash or protrusions shall not exceed 0.15 mm per side.

Dimension is the length of terminal for soldering to a substrate.

Terminal positions are shown for reference only.

6. Formed leads shall be planar with respect to one another within 0.10 mm at seating plane.

The lead width dimension does not include Dambar protrusion. Allowable Dambar protrusion shall be 0.08 mm total in excess of the lead width dimension at maximum material condition. Dambar cannot be located on the lower radius or the lead foot. Minimum space between protrusions and an adjacent lead to be 0.14 mm. See detail "B" and Section "C-C".

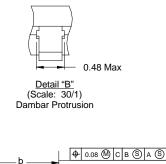
/8. Section "C-C" to be determined at 0.10 mm to 0.25 mm from the lead tip.

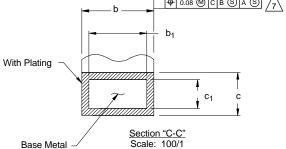
9. Controlling dimension: millimeters.

10. This part is compliant with JEDEC registration MO-187, variation AA and BA.

11 Datums -A- and -B- to be determined Datum plane -H-.

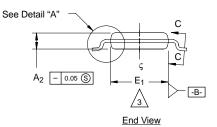
12 Exposed pad area in bottom side is the same as teh leadframe pad size.









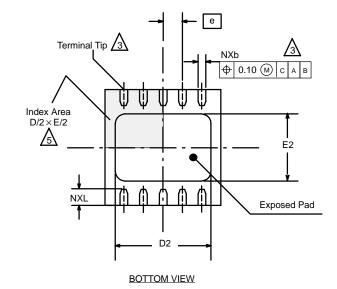


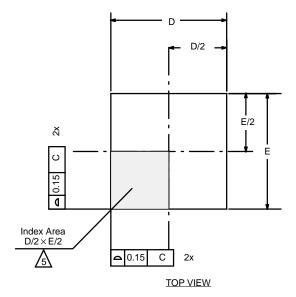
N = 10L

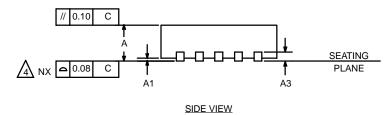
	М	MILLIMETERS				
Dim	Min	Nom	Max	Note		
Α	-	-	1.10			
A <sub>1</sub>	0.05	0.10	0.15			
A <sub>2</sub>	0.75	0.85	0.95			
b	0.17	-	0.27	8		
b <sub>1</sub>	0.17	0.20	0.23	8		
С	0.13	-	0.23			
<b>c</b> <sub>1</sub>	0.13	0.15	0.18			
D		3.00 BSC		3		
Е		4.90 BSC				
E <sub>1</sub>	2.90	3.00	3.10	3		
е		0.50 BSC				
е <sub>1</sub>		2.00 BSC				
L	0.40	0.55	0.70	4		
Ν		5				
x	0°	4°	6°			
CN: T-02 DWG: 58	2080—Rev. 0 67	C, 15-Jul-02				



### DFN-10 LEAD (3 X 3)







	Dim	MILLIMETERS			INCHES		
		Min	Nom	Max	Min	Nom	Max
	Α	0.80	0.90	1.00	0.031	0.035	0.039
and inches.	A1	0.00	0.02	0.05	0.000	0.001	0.002
	A3	0.20 BSC			0.008 BSC		
terminal and is measured terminal tip.	b	0.18	0.23	0.30	0.007	0.009	0.012
d heat sink slug as well as the	D	3.00 BSC			0.118 BSC		
C C	D2	2.20	2.38	2.48	0.087	0.094	0.098
r a mold or marked feature, it ndicated.	E	3.00 BSC			0.118 BSC		
luicaleu.	E2	1.49	1.64	1.74	0.059	0.065	0.069
	е	0.50 BSC			0.020 BSC		
	L	0.30	0.40	0.50	0.012	0.016	0.020
	*Use millir	neters as the	primary meas	surement.	•	•	
	ECN: S-42 DWG: 594		4, 29-Nov-04				

#### NOTES:

- 1. All dimensions are in millimeters and inches.
- 2. N is the total number of terminals.



<u>/5</u>

Dimension b applies to metallized terminal and is between 0.15 and 0.30 mm from terminal tip.

Coplanarity applies to the exposed heat sink slug as well as the terminal.

The pin #1 identifier may be either a mold or marked feature, it must be located within the zone iindicated.



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